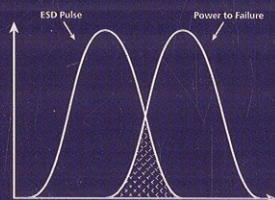


ESD

FAILURE MECHANISMS AND MODELS

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 WILEY



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